

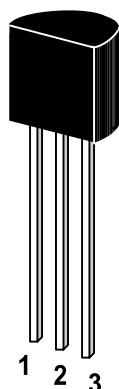
ST 2SD1616 / 2SD1616A

NPN Silicon Transistor

The 2SD1616 / 2SD1616A are designed for use in driver and output stages of AF amplifier general purpose application.

The transistor is subdivided into three groups R, O and Y, according to its DC current gain

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

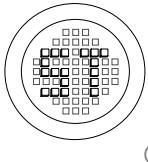
TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^{\circ}\text{C}$)

		Symbol	Value	Unit
Collector Base Voltage	2SD1616	V_{CBO}	60	V
	2SD1616A		120	
Collector Emitter Voltage	2SD1616	V_{CEO}	50	V
	2SD1616A		60	
Emitter Base Voltage		V_{EBO}	6	V
Collector Current (DC)		I_C	1	A
Collector Current (pulse) ¹⁾		I_C	2	A
Power Dissipation		P_{tot}	0.75	W
Junction Temperature		T_j	150	?
Storage Temperature Range		T_s	-55 to +150	?

1) PW? 10ms, Duty Cycle? 50%

G S P FORM A IS AVAILABLE



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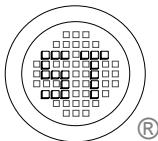
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Characteristics at $T_{amb}=25^{\circ}\text{C}$

		Symbol	Min.	Typ.	Max.	Unit
DC Current Gain ²⁾ at $V_{CE}=2\text{V}$, $I_C=100\text{mA}$	R	h_{FE}	135	-	270	-
	O	h_{FE}	200	-	400	-
	Y	h_{FE}	300	-	600	-
		h_{FE}	81	-	-	-
Base Emitter Voltage ²⁾ at $V_{CE}=2\text{V}$, $I_C=50\text{mA}$	V_{BE}		600		700	mV
Collector Cutoff Current at $V_{CB}=60\text{V}/120\text{V}$	I_{CBO}		-	-	100	nA
Emitter Cutoff Current at $V_{EB}=6\text{V}$	I_{EBO}		-	-	100	nA
Collector Saturation Voltage ²⁾ at $I_C=1\text{A}$, $I_B=50\text{mA}$	$V_{CE(\text{sat})}$		-	0.15	0.3	V
Base Saturation Voltage ²⁾ at $I_C=1\text{A}$, $I_B=50\text{mA}$	$V_{BE(\text{sat})}$		-	0.9	1.2	V
Gain Bandwidth Product at $V_{CE}=2\text{V}$, $I_C=-100\text{mA}$	f_T		100	160	-	MHz
Output Capacitance at $V_{CB}=10\text{V}$, $f=1\text{MHz}$	C_{OB}		-	19	-	pF
Turn-on Time	at $V_{CC}=10\text{V}$, $I_C=-100\text{mA}$ $I_{B1}=-I_{B2}=10\text{ mA}$ $V_{BE(\text{off})}=-2$ to 3 V	t_{on}	-	0.07	-	μs
Storage Time		t_{stg}	-	0.95	-	μs
Fall Time		t_f	-	0.07	-	μs

2) Pulsed PW $\leq 350\mu\text{s}$, Duty Cycle $\leq 2\%$

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SEMTECH ELECTRONICS LTD.

(Subsidiary of Semtech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001
Certificate No. 7116



ISO 9001 : 2000
Certificate No. 956-1994-25-24

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